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### Vishay Semiconductors

# Hyperfast Rectifier, 8 A FRED Pt®



TO-220 FullPAK 2L



VS-8ETH06FP-N3

PRIMARY CHARACTERISTICS				
I <sub>F(AV)</sub>	8 A			
V <sub>R</sub>	600 V			
V <sub>F</sub> at I <sub>F</sub>	1.3 V			
t <sub>rr</sub> typ.	18 ns			
T <sub>J</sub> max.	175 °C			
Package	TO-220 FullPAK 2L			
Circuit configuration	Single			

#### **FEATURES**

- · Hyperfast recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- · Low leakage current
- Fully isolated package (V<sub>INS</sub> = 2500 V<sub>RMS</sub>)
- Designed and qualified according to JEDEC®-JESD 47
- Material categorization: for definitions of compliance please see <a href="https://www.vishav.com/doc?99912"><u>www.vishav.com/doc?99912</u></a>

#### **DESCRIPTION / APPLICATIONS**

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Repetitive peak reverse voltage	V <sub>RRM</sub>		600	V
Average rectified forward current	I <sub>F(AV)</sub>	T <sub>C</sub> = 108 °C	8	
Non-repetitive peak surge current	I <sub>FSM</sub>		100	Α
Repetitive peak forward current	I <sub>FM</sub>		16	
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		-65 to +175	°C

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS MIN.		TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	$V_{BR}$ , $V_{R}$	Ι <sub>R</sub> = 100 μΑ	600	-	-	.,
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 8 A	-	2.0	2.4	V
	VF	I <sub>F</sub> = 8 A, T <sub>J</sub> = 150 °C	-	1.3	1.8	
Devenue leekees euwent		$V_R = V_R$ rated	-	0.3	50	
Reverse leakage current I <sub>R</sub>		$T_J = 150  ^{\circ}\text{C},  V_R = V_R  \text{rated}$	-	55	500	μA
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 600 V	-	17	-	pF
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	8.0	-	nΗ



<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>C</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST	TEST CONDITIONS		TYP.	MAX.	UNITS
		$I_F = 1 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	18	22	
Reverse recovery time	_	$I_F = 8 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	20	25	
neverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	25	-	ns
		T <sub>J</sub> = 125 °C		-	40	=.	
Deels received a surrout		T <sub>J</sub> = 25 °C	$I_F = 8 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 390 \text{ V}$	-	2.4	=.	А
Peak recovery current	Peak recovery current I <sub>RRM</sub>	T <sub>J</sub> = 125 °C		-	4.8	-	
Poverse receivery charge	rge Q <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	25	=.	nC
Reverse recovery charge		T <sub>J</sub> = 125 °C		-	120	=.	IIC
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 125 °C	$I_F = 8 A$ $dI_F/dt = 600 A/\mu s$ $V_R = 390 V$	-	33	-	ns
Peak recovery current	I <sub>RRM</sub>			-	12	-	Α
Reverse recovery charge	$Q_{rr}$			-	220	-	nC

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65	-	175	°C
Thermal resistance, junction-to-case	R <sub>thJC</sub>		-	3.4	4.3	°C/W
Thermal resistance, junction-to-ambient per leg	R <sub>thJA</sub>	Typical socket mount	-	-	70	
Thermal resistance, case-to-heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth, and greased	-	0.5	-	
Weight			-	2.0	-	g
vveignt			-	0.07	-	oz.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking device		Case style TO-220 FullPAK 2L	8ETH06FP			

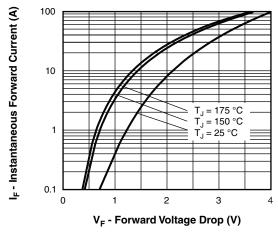


Fig. 1 - Typical Forward Voltage Drop Characteristics

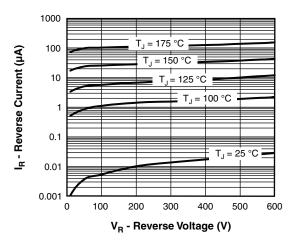


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

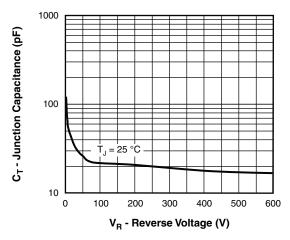


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

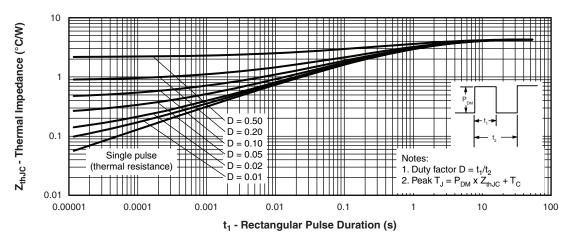


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics

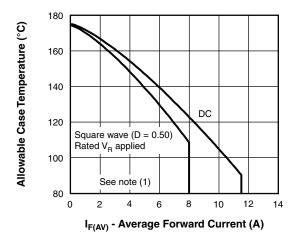


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

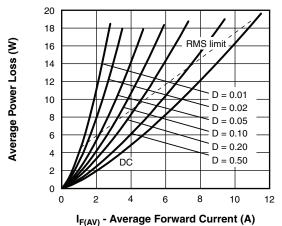


Fig. 6 - Forward Power Loss Characteristics

#### Note

 $\begin{array}{ll} \text{(1)} & \text{Formula used: } T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}; \\ Pd = \text{forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 5)}; \\ Pd_{REV} = \text{inverse power loss} = V_{R1} \times I_R \text{ (1 - D)}; I_R \text{ at } V_{R1} = \text{rated } V_R \\ \end{array}$ 



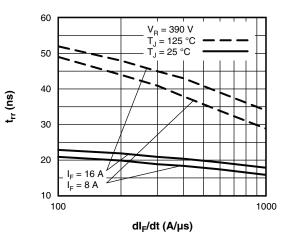


Fig. 7 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

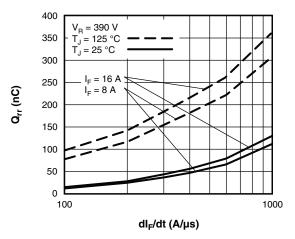
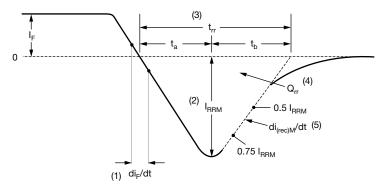


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt



- (1) di<sub>F</sub>/dt rate of change of current through zero crossing
- (2) I<sub>RRM</sub> peak reverse recovery current
- (3)  $\rm t_{rr}$  reverse recovery time measured from zero crossing point of negative going  $\rm I_F$  to point where a line passing through 0.75  $\rm I_{RRM}$  and 0.50  $\rm I_{RRM}$  extrapolated to zero current.
- (4)  $\mathbf{Q}_{rr}$  area under curve defined by  $\mathbf{t}_{rr}$  and  $\mathbf{I}_{RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

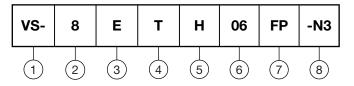
(5) di<sub>(rec)M</sub>/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 9 - Reverse Recovery Waveform and Definitions



#### **ORDERING INFORMATION TABLE**

**Device code** 



Vishay Semiconductors product

2 - Current rating (8 = 8 A)

**3** - E = single

- T = TO-220,  $D^2PAK$  (TO-263AB)

- H = hyperfast recovery

6 - Voltage rating (06 = 600 V)

- FP = TO-220 FullPAK 2L

8 - Environmental digit:

-N3 = halogen-free, RoHS-compliant, and totally lead (Pb)-free

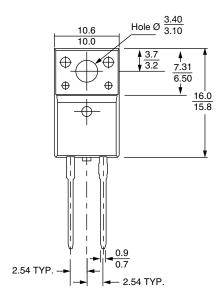
ORDERING INFORMATION (Example)					
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-8ETH06FP-N3	50	1000	Antistatic plastic tube		

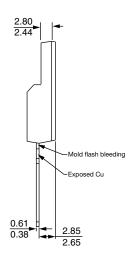
LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?96157			
Part marking information	www.vishay.com/doc?95392			

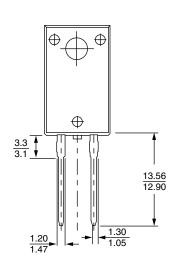


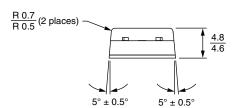
### 2L TO-220 FullPAK

#### **DIMENSIONS** in millimeters









Bottom view



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